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**Inventor Name Search Result**

Your Search was:

Last Name = FALSTER

First Name = ROBERT

Application#	Patent#	Status	Date Filed	Title	Inventor Name 50
<u>60259362</u>	Not Issued	159	01/02/2001	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	FALSTER, ROBERT J.
<u>60252715</u>	Not Issued	159	11/22/2000	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	FALSTER, ROBERT J.
<u>60245610</u>	Not Issued	159	11/03/2000	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	FALSTER, ROBERT
<u>60175506</u>	Not Issued	159	01/11/2000	PROCESS FOR DETECTING AGGLOMERATED INTRINSIC POINT DEFECTS BY METAL DECORATION	FALSTER, ROBERT
<u>60155725</u>	Not Issued	159	09/23/1999	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	FALSTER, ROBERT
<u>60095878</u>	Not Issued	159	08/10/1998	PROCESS FOR PREPARATION OF SILICON ON INSULATOR SUBSTRATES WITH IMPROVED RESISTANCE TO FORMATION OF METAL PRECIPITATES	FALSTER, ROBERT
<u>60095877</u>	Not Issued	159	08/10/1998	PROCESS FOR PREPARATION OF SILICON ON INSULATOR SUBSTRATES WITH IMPROVED RESISTANCE TO FORMATION OF METAL PRECIPITATES	FALSTER, ROBERT

<u>60062316</u>	Not Issued	159	10/17/1997	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT
<u>60047888</u>	Not Issued	159	05/29/1997	PROCESS FOR THE REMOVAL OF COPPER FROM POLISHED BORON DOPED SILICON WAFERS	FALSTER, ROBERT
<u>60041845</u>	Not Issued	159	04/09/1997	LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	FALSTER, ROBERT
<u>11089102</u>	Not Issued	020	03/24/2005	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	FALSTER, ROBERT J.
<u>11082267</u>	Not Issued	030	03/17/2005	CONTROL OF THERMAL DONOR FORMATION IN HIGH RESISTIVITY CZ SILICON	FALSTER, ROBERT J.
<u>11058996</u>	Not Issued	020	02/16/2005	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT J.
<u>11058885</u>	Not Issued	020	02/16/2005	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	FALSTER, ROBERT J.
<u>10639737</u>	Not Issued	168	08/12/2003	LOW DEFECT DENSITY SILICON	FALSTER, ROBERT J.
<u>10615127</u>	Not Issued	071	07/08/2003	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	FALSTER, ROBERT J.
<u>10460901</u>	6713370	150	06/13/2003	PROCESS FOR THE PREPARATION OF AN IDEAL OXYGEN PRECIPITATING SILICON WAFER CAPABLE OF FORMING AN ENHANCED DENUDED ZONE	FALSTER, ROBERT J.
<u>10441413</u>	Not Issued	030	05/20/2003	SINGLE CRYSTAL SILICON WAFER HAVING AN EPITAXIAL LAYER SUBSTANTIALLY FREE FROM GROWN-IN DEFECTS	FALSTER, ROBERT J.
<u>10437141</u>	Not Issued	094	05/13/2003	PROCESS FOR COOLING A SILICON INGOT HAVING A VACANCY DOMINATED REGION TO PRODUCE DEFECT FREE SILICON	FALSTER, ROBERT J.
<u>10430798</u>	6849119	150	05/06/2003	IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT J.

				WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	
<u>10430483</u>	Not Issued	041	05/06/2003	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	FALSTER, ROBERT J.
<u>10373899</u>	6896728	150	02/25/2003	PROCESS FOR PRODUCING LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT J.
<u>10189139</u>	Not Issued	093	07/03/2002	VACANCY, DOMINATED, DEFECT-FREE SILICON	FALSTER, ROBERT J.
<u>10177444</u>	Not Issued	092	06/21/2002	SILICON ON INSULATOR STRUTURE HAVING AN EPITAXIAL LAYER AND INTRINSIC GETTERING	FALSTER, ROBERT J.
<u>10135597</u>	6632278	150	04/30/2002	LOW DEFECT DENSITY EPITAXIAL WAFER AND A PROCESS FOR THE PREPARATION THEREOF	FALSTER, ROBERT J.
<u>10135174</u>	6605150	150	04/30/2002	LOW DEFECT DENSITY REGIONS OF SELF-INTERSTITIAL DOMINATED SILICON	FALSTER, ROBERT J.
<u>09928739</u>	6537368	150	08/13/2001	IDEAL OXYGEN PRECIPITATING EPITAXIAL SILICON WAFERS AND OXYGEN OUT-DIFFUSION-LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>09737715</u>	6342725	150	12/15/2000	SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY HANDLE WAFER AND PROCESS FOR THE PREPARATION THEREOF	FALSTER, ROBERT J.
<u>09705092</u>	6555194	150	11/02/2000	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT J.
<u>09704900</u>	6579779	150	11/02/2000	A PROCESS FOR THE PREPARATION OF AN IDEAL OXYGEN PRECIPITATING SILICON WAFER HAVING AN ASYMMETRICAL VACANCY	FALSTER, ROBERT J.

				CONCENTRATION PROFILE CAPABLE OF FORMING AN ENHANCED DENUDED ZONE	
<u>09704893</u>	<u>6586068</u>	150	11/02/2000	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT- DIFFUSION-LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>09661822</u>	<u>6391662</u>	150	09/14/2000	PROCESS FOR DETECTING AGGLOMERATED INTRINSIC POINT DEFECTS BY METAL DECORATION	FALSTER, ROBERT J.
<u>09661745</u>	Not Issued	161	09/14/2000	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	FALSTER, ROBERT J.
<u>09626635</u>	<u>6306733</u>	150	07/27/2000	IDEAL OXYGEN PRECIPITATING EPITAXIAL SILICON WAFERS AND OXYGEN OUT-DIFFUSION- LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>09475320</u>	<u>6638357</u>	150	12/30/1999	METHOD FOR REVEALING AGGLOMERATED INTRINSIC POINT DEFECTS IN SEMICONDUCTOR CRYSTALS	FALSTER, ROBERT
<u>09371668</u>	Not Issued	161	08/10/1999	PROCESS FOR PREPARATION OF SILICON ON INSULATOR SUBSTRATES WITH IMPROVED RESISTANCE TO FORMATION OF METAL PRECIPITATES	FALSTER, ROBERT
<u>09370447</u>	Not Issued	161	08/10/1999	PROCESS FOR PREPARATION OF SILICON ON INSULATOR SUBSTRATES WITH IMPROVED RESISTANCE TO FORMATION OF METAL PRECIPITATES	FALSTER, ROBERT
<u>09344036</u>	<u>6312516</u>	150	06/25/1999	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	FALSTER, ROBERT J.

<u>09340489</u>	<u>6204152</u>	150	06/30/1999	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT- DIFFUSION-LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>09057800</u>	<u>6190631</u>	150	04/09/1998	LOW DEFECT DENSITY, IDEAL OXYGEN PRECIPITATING SILICON	FALSTER, ROBERT J
<u>09030110</u>	<u>6180220</u>	150	02/25/1998	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT- DIFFUSION- LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>08934946</u>	<u>5882989</u>	150	09/22/1997	PROCESS FOR THE PREPARATION OF SILICON WAFERS HAVING A CONTROLLED DISTRIBUTION OF OXYGEN PRECIPITATE NUCLEATION CENTERS	FALSTER, ROBERT
<u>08806436</u>	<u>5994761</u>	150	02/26/1997	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT- DIFFUSION-LESS PROCESS THEREFOR	FALSTER, ROBERT
<u>08403301</u>	<u>5593494</u>	150	03/14/1995	PRECISION CONTROLLED PRECIPITATION OF OXYGEN IN SILICON	FALSTER, ROBERT
<u>08084405</u>	<u>5418172</u>	150	06/29/1993	METHOD FOR DETECTING SOURCES OF CONTAMINATION IN SILICON USING A CONTAMINATION MONITOR WAFER	FALSTER, ROBERT
<u>08064013</u>	<u>5403406</u>	150	05/13/1993	SILICON WAFER HAVING CONTROLLED PRECIPITATION DISTRIBUTION	FALSTER, ROBERT
<u>08062926</u>	<u>5401669</u>	150	05/17/1993	PROCESS FOR THE PREPARATION OF SILICON WAFERS HAVING CONTROLLED DISTRIBUTION OF OXYGEN PRECIPITATE NUCLEATION CENTERS	FALSTER, ROBERT
<u>07971056</u>	<u>5272119</u>	150	11/03/1992	PROCESS FOR CONTAMINATE REMOVAL AND MINORITY CARRIER LIFETIME IMPROVEMENT	FALSTER, ROBERT

				IN SILICON.	
<u>07736055</u>	<u>5262646</u>	150	07/26/1991	INFRA-RED SCANNING MICROSCOPY	FALSTER, ROBERT

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**Inventor Name Search Result**

Your Search was:

Last Name = FALSTER

First Name = ROBERT J.

Application#	Patent#	Status	Date Filed	Title	Inventor Name 29
<u>60125895</u>	Not Issued	159	03/24/1999	VACANCY AND SELF-INTERSTITIAL CONCENTRATIONS IN GROWING SILICON CRYSTALS	FALSTER, ROBERT J.
<u>60117623</u>	Not Issued	159	01/28/1999	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	FALSTER, ROBERT J.
<u>60104304</u>	Not Issued	159	10/14/1998	THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	FALSTER, ROBERT J.
<u>60104303</u>	Not Issued	159	10/14/1998	LOW DEFECT DENSITY SILICON	FALSTER, ROBERT J.
<u>60104288</u>	Not Issued	159	10/14/1998	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS	FALSTER, ROBERT J.
<u>60104087</u>	Not Issued	159	10/14/1998	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS AT ARBITRARY GROWTH RATES MAXIMUM THROUGHPUT	FALSTER, ROBERT J.
<u>60098921</u>	Not Issued	159	09/02/1998	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETERING	FALSTER, ROBERT J.
<u>60098902</u>	Not Issued	159	09/02/1998	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	FALSTER, ROBERT J.
<u>60098861</u>	Not Issued	159	09/02/1998	IDEAL OXYGEN PRECIPITATING SILICON WAFERS AND OXYGEN OUT-	FALSTER, ROBERT J.

				DIFFUSION-LESS PROCESS THEREFOR	
<u>60098822</u>	Not Issued	159	09/02/1998	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	FALSTER, ROBERT J.
<u>60098808</u>	Not Issued	159	09/02/1998	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	FALSTER, ROBERT J.
<u>60095407</u>	Not Issued	159	08/05/1998	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	FALSTER, ROBERT J.
<u>60090723</u>	Not Issued	159	06/26/1998	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS	FALSTER, ROBERT J.
<u>09417610</u>	<u>6284039</u>	150	10/13/1999	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN - IN DEFECTS	FALSTER, ROBERT J.
<u>09416998</u>	<u>6416836</u>	150	10/13/1999	THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	FALSTER, ROBERT J.
<u>09387288</u>	<u>6236104</u>	150	08/31/1999	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON	FALSTER, ROBERT J.
<u>09385108</u>	<u>6361619</u>	150	08/27/1999	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING	FALSTER, ROBERT J.
<u>09384669</u>	<u>6191010</u>	150	08/27/1999	PROCESS FOR PREPARING AN IDEAL OXYGEN PRECIPITATING SILICON WAFER	FALSTER, ROBERT J.
<u>09379383</u>	<u>6336968</u>	150	08/23/1999	NON-OXYGEN PRECIPITATING CZOCHRALSKI SILICON WAFERS	FALSTER, ROBERT J.
<u>09366850</u>	<u>6828690</u>	150	08/04/1999	NON-UNIFORM MINORITY CARRIER LIFETIME DISTRIBUTIONS IN HIGH PERFORMANCE SILICON POWER DEVICES	FALSTER, ROBERT J.



<a href="#">09344709</a>	<a href="#">6328795</a>	150	06/25/1999	PROCESS FOR GROWTH OF DEFECT FREE SILICON CRYSTALS OF ARBITRARILY LARGE DIAMETERS	FALSTER, ROBERT J.
<a href="#">09270366</a>	<a href="#">6379642</a>	150	03/16/1999	VACANCY DOMINATED, DEFECT-FREE SILICON	FALSTER, ROBERT J.
<a href="#">09082905</a>	<a href="#">6100167</a>	150	05/21/1998	PROCESS FOR THE REMOVAL OF COPPER FROM POLISHED BORON DOPED SILICON WAFERS	FALSTER, ROBERT J.
<a href="#">09057907</a>	<a href="#">6287380</a>	150	04/09/1998	LOW DEFECT DENSITY SILICON	FALSTER, ROBERT J.
<a href="#">09057851</a>	<a href="#">5919302</a>	150	04/09/1998	LOW DEFECT DENSITY VACANCY DOMINATED SILICON	FALSTER, ROBERT J.
<a href="#">09057801</a>	<a href="#">6254672</a>	150	04/09/1998	LOW DEFECT DENSITY SELF-INTERSTITIAL DOMINATED SILICON	FALSTER, ROBERT J.
<a href="#">08865912</a>	Not Issued	161	05/30/1997	PROCESS FOR CONTROLLING THERMAL HISTORY OF CZOCHRALSKI-GROWN SILICON	FALSTER, ROBERT J.
<a href="#">08694157</a>	<a href="#">5779791</a>	150	08/08/1996	PROCESS FOR CONTROLLING THERMAL HISTORY OF CZOCHRALSKI-GROWN SILICON	FALSTER, ROBERT J.

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 PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = VORONKOV

First Name = VLADIMIR

Application#	Patent#	Status	Date Filed	Title	Inventor Name 20
<u>60323827</u>	Not Issued	159	09/21/2001	ANALYTICAL METHOD TO MEASURE NITROGEN CONCENTRATION IN SINGLE CRYSTAL SILICON	VORONKOV, VLADIMIR
<u>60252715</u>	Not Issued	159	11/22/2000	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	VORONKOV, VLADIMIR V.
<u>60245610</u>	Not Issued	159	11/03/2000	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	VORONKOV, VLADIMIR
<u>60125895</u>	Not Issued	159	03/24/1999	VACANCY AND SELF-INTERSTITIAL CONCENTRATIONS IN GROWING SILICON CRYSTALS	VORONKOV, VLADIMIR V.
<u>60117623</u>	Not Issued	159	01/28/1999	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	VORONKOV, VLADIMIR
<u>11089102</u>	Not Issued	020	03/24/2005	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	VORONKOV, VLADIMIR V.
<u>10615127</u>	Not Issued	071	07/08/2003	PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING SILICON WAFER	VORONKOV, VLADIMIR V.
<u>10430483</u>	Not Issued	041	05/06/2003	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE	VORONKOV, VLADIMIR V.

				COOLING RATE THROUGH NUCLEATION	
<u>10260239</u>	<u>6652646</u>	150	09/30/2002	PROCESS FOR GROWING A SILICON CRYSTAL SEGMENT SUBSTANTIALLY FREE FROM AGGLOMERATED INTRINSIC POINT DEFECTS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS	VORONKOV, VLADIMIR
<u>10252479</u>	<u>6803576</u>	150	09/23/2002	ANALYTICAL METHOD TO MEASURE NITROGEN CONCENTRATION IN SINGLE CRYSTAL SILICON	VORONKOV, VLADIMIR
<u>10039196</u>	Not Issued	094	01/02/2002	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY	VORONKOV, VLADIMIR V.
<u>10008812</u>	<u>6726764</u>	150	11/13/2001	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS	VORONKOV, VLADIMIR V.
<u>09972608</u>	<u>6858307</u>	150	10/05/2001	METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON	VORONKOV, VLADIMIR V.
<u>09871255</u>	<u>6689209</u>	150	05/31/2001	PROCESS FOR PREPARING LOW DEFECT DENSITY SILICON USING HIGH GROWTH RATES	VORONKOV, VLADIMIR
<u>09853232</u>	<u>6500255</u>	150	05/11/2001	PROCESS FOR GROWING SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS WHILE SUPPRESSING THE FORMATION OF AGGLOMERATED INTRINSIC POINT DEFECTS	VORONKOV, VLADIMIR
<u>09661745</u>	Not Issued	161	09/14/2000	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH NUCLEATION	VORONKOV, VLADIMIR V.

<u>09495563</u>	Not Issued	161	02/01/2000	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS	VORONKOV, VLADIMIR V.
<u>09344036</u>	<u>6312516</u>	150	06/25/1999	PROCESS FOR PREPARING DEFECT FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS	VORONKOV, VLADIMIR

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